

/ Descriptions

KF \$O) CD GE G` Silicon PNP transistor in a TO-92LM Plastic Package.

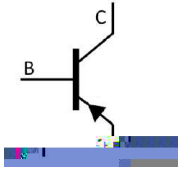
/ Features

\$) J; (/ -)
Low $V_{CE(sat)}$, complements the 2SD1862.

/ Applications

Medium power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-2.0	A
Collector Current-Peak	I_{CM}	-3.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\mu A$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-32			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-50\mu A$ $I_C=0$				V

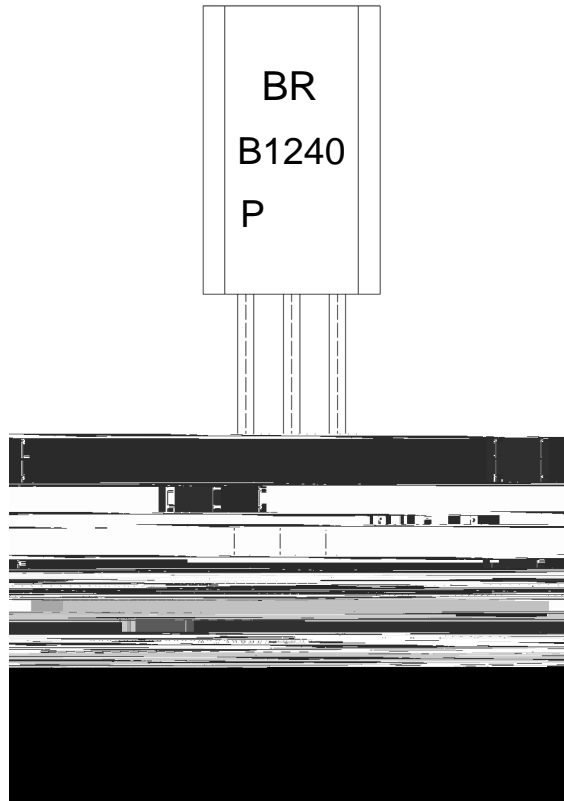
2SB1240

28 TccTw(2S9.5(-D)-10.9(A)95.8(T20161(A)03 5(S (H)3 5(EET)TJ3.9860 0 13.08 62.94 708 62527.6m-0.0018 Tc00B1240)

2SB1240
Rev.E Mar.-2016

/ Package Dimensions

/ Marking Instructions



9| 1
9() +
G1

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Note:

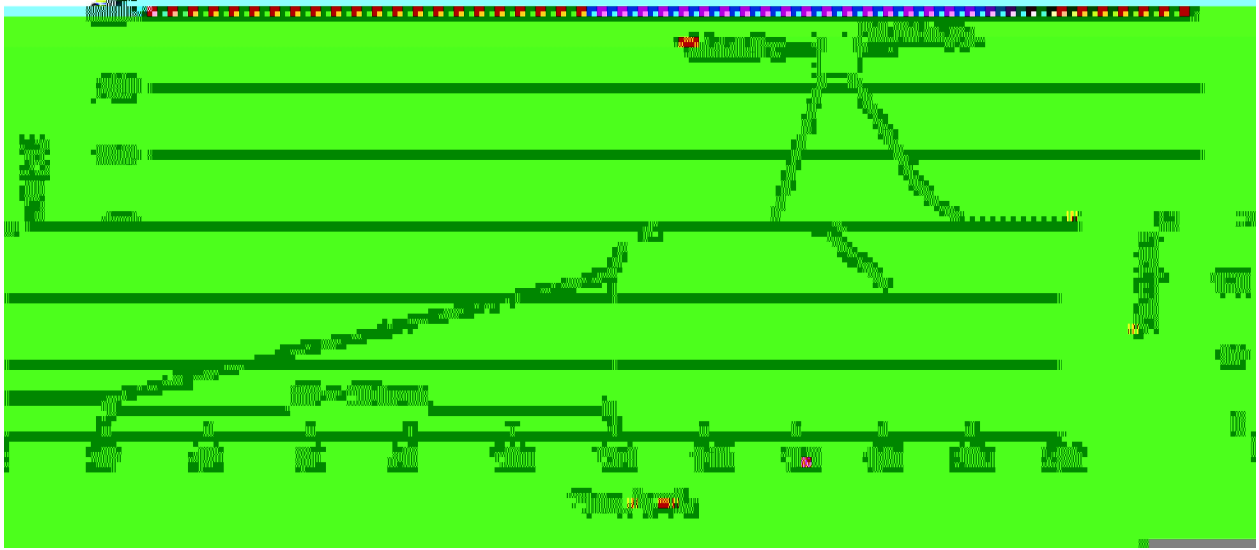
BR: Company Code.

B1240: Product Type.

P: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- | | | | | | | |
|---|--------|-----|------------|--------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | Note: | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. | |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units				Dimension		(unit mm3)

/ AMMO

Package Type	Units				Dimension		(unit mm3)